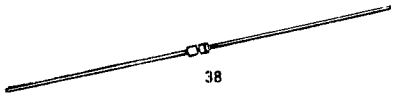


38

SIGNAL DIODES

100 – 200 MA TYPES

Part Number	BV @ 100μA Min. (V)	I_R @ 25°C Max. (nA)	@ V_R(V)	V_F Max. (V)	@ I_F(mA)	C_O @ 0V (pf)	t_{rr} (nsec)	Package Type	Package Outline No.
1N4150 *	50	100	50	1.00	200	2.5	4	DO35	38
1N4450	30	50	30	1.00	200	4	4	DO35	38
1N4606	85	100	50	1.00	200	2.5	4	DO35	38

200 – 400 MA TYPES

Part Number	BV @ 100μA Min. (V)	I_R @ 25°C Max. (nA)	@ V_R(V)	V_F Max. (V)	@ I_F(mA)	C_O @ 0V (pf)	t_{rr} (nsec)	Package Type	Package Outline No.
1N4451	40	50	30	1.00	300	6	10	DO35	38
1N4607	85	100	50	1.00	400	4	10	DO35	38
1N4608	85	100	50	.96	400	4	10	DO35	38
DT230C	300	1000	300	1.20	250	5	300	DO35	38
DT230H	250	1000	250	1.00	200	5	300	DO35	38
DT230HI	250	1000	250	1.10	250	5	300	DO35	38
DT230B	200	1000	200	1.10	250	5	300	DO35	38
DT230G	150	1000	150	1.10	250	5	300	DO35	38
DT230A	100	1000	100	1.10	250	5	300	DO35	38
DT230F	50	1000	50	1.10	250	5	300	DO35	38

* JAN and JANTX types available

MULTIPELLET SILICON SIGNAL DIODES

40, 41, 42

Part Number	BV @ 5μA (V)	I_R @ 25°C Max. (nA)	@ V_R(V)	V_F Max. (V)	@ I_F(mA)	C_O @ 0V Max. (pf)	t_{rr} (nsec)	Package Type	Package Outline No.
1N4156	30	50	20	1.58	10	25	—	DO35	42
1N4157	30	50	20	2.32	10	20	—	DO35	41
1N4453	30	50	20	.800	10	30	—	DO35	38
1N4828	30	100	20	.830	10	35	—	DO35	38
1N4829	30 [1]	100	20	1.61	10	25	—	DO35	42
1N4830	30 [1]	100	20	2.35	10	20	—	DO35	41
1N5179	30	50	20	3.20	10	20	—	DO35	40
MPD200	70	30	30	1.54	10	15	—	DO35	42
MPD201	50	50	20	1.57	10	15	—	DO35	42
MPD202	50	90	20	1.60	10	15	—	DO35	42
MPD203	50	90	20	1.51	10	15	—	DO35	42
STB567	50	500	20	1.61	10	15	—	DO35	42
MPD300	100	30	30	2.33	10	10	—	DO35	41
MPD301	60	40	20	2.32	10	10	—	DO35	41
MPD302	60	90	20	2.32	10	10	—	DO35	41
STB568	60	500	20	2.31	10	10	—	DO35	41
MPD400	120	30	30	3.07	10	7	—	DO35	40
MPD401	75	50	20	3.01	10	7	—	DO35	40
MPD402	75	90	20	3.01	10	7	—	DO35	40
STB569	75	500	20	3.01	10	7	—	DO35	40

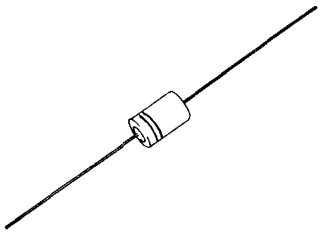
[1] Measured @ 100μA

Silicon Diodes

STABISTORS

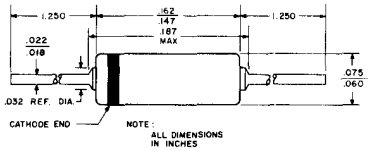
STB567, 8, 9

These low-cost General Electric Stabistors are multi-pellet diodes which have a tightly controlled conductance at $I_F = 10mA$. They consist of 2, 3, or 4 planar passivated epitaxial diode pellets in series, mounted in a subminiature double-heatsink package. The STB567, STB568, and STB569 are examples of such diodes with 2, 3, and 4 pellets respectively. These diodes can be used as low voltage regulator diodes or to maintain a bias on the output transistor of push-pull amplifiers. Multi-Pellet Stabistors maintain LINEAR temperature response (in millivolts per degree C) over the ambient temperature range of −55°C to +175°C. Nominal change in voltage for the STB567, STB568, and STB569 is 4mV, 6mV, and 8mV respectively for each degree C change in ambient temperature.

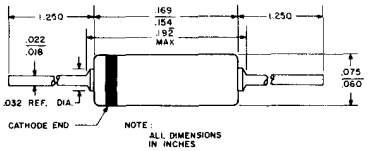


absolute maximum ratings: (25°C) (unless otherwise specified)

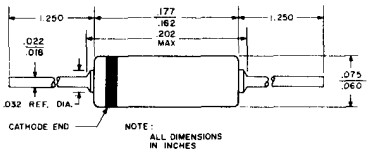
Voltage		
Reverse (continuous)	12	volts
Power		
Dissipation	400	mW
(Derate: 2.67 mW/°C for Ambient Temperature above 25°C)		
Temperature		
Operating	−65 to +175	°C
Storage	−65 to +200	°C
Lead ($\frac{1}{16} \pm \frac{1}{32}$ inch from case for 10 sec)	300	°C



STB567



STB568



STB569

NOTES

1. ALL DIMENSIONS ARE IN INCHES AND ARE REFERENCE UNLESS TOLERANCED

electrical characteristics: (25°C) (unless otherwise specified)

	STB567		STB568		STB569		
	Min.	Max.	Min.	Max.	Min.	Max.	
Forward Voltage*							
$I_F = 10mA$	1.31	1.61	2.09	2.31	2.72	3.01	Volts
Breakdown Voltage							
$I_R = 5\mu A$	12		12		12		Volts

***Forward Voltage Tolerances:**

STB567	1.46 ± 10%
STB568	2.20 ± 5%
STB569	2.87 ± 5%